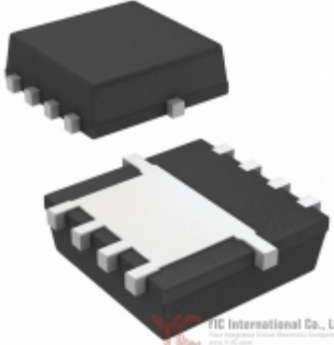




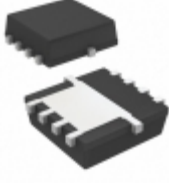
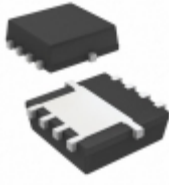



	<b>SI7810DN-T1-E3</b>
	<b>Hersteller-Teilenummer:</b> <a href="#">SI7810DN-T1-E3</a>
	<b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a>
	<b>Teil der Beschreibung:</b> MOSFET N-CH 100V 3.4A 1212-8
<b>Datenblätter:</b>  <a href="#">SI7810DN-T1-E3.pdf</a>	<b>RoHs Status:</b> Bleifrei / RoHS-konform
<b>Lagerzustand:</b> New original, 50574 pcs Stock Available.	<b>Liefern von:</b> Hong Kong
<b>Image may be representation. See specs for product details.</b>	<b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS

### Spezifikationen

Teilenummer	<a href="#">SI7810DN-T1-E3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET N-CH 100V 3.4A 1212-8
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	50574 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	1.5W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.4A (Ta)
Rds On (Max) @ Id, Vgs	62 mOhm @ 5.4A, 10V
VGS (th) (Max) @ Id	4.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	17nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	-
Antriebsspannung (Max Rds On, Min Rds On)	6V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)












SI7810DN-T1-E3 ist neu im Original, Suche SI7810DN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7810DN-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7810DN-T1-E3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI7812DN</b> SI SI7812DN SI</p>	 <p><b>SI7810DN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 100V 3.4A 1212-8</p>	 <p><b>SI7810DN-T1-E</b> VISHAY SI7810DN-T1-E VISHAY</p>	 <p><b>SI7810DN-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 100V 3.4A 1212-8</p>
 <p><b>SI7810DN-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 100V 3.4A 1212-8</p>	 <p><b>SI7810DN</b> VISHAY SI7810DN VISHAY</p>	 <p><b>SI7810DN-T1</b> VISHAY SI7810DN-T1 VISHAY</p>	 <p><b>SI7806DN-T1-GE3</b> VB SI7806DN-T1-GE3 VB</p>

### heiße Teile

Mehr

 SI7790DP-T1-GE3	 SI7790DP-T1-GE3	 SI7792DP-T1-GE3	 SI7792DP-T1-GE3	 SI7794DP-T1-GE3
 SI7794DP-T1-GE3	 SI7798DP-T1-GE3	 SI7804DN	 SI7804DN-T1-E3	 SI7804DN-T1-E3
 SI7806ADN	 SI7806ADN-T1-E3	 SI7806ADN-T1-E3	 SI7806ADN-T1-E3-PBF	 SI7806ADN-T1-GE3
 SI7806ADN-T1-GE3	 SI7806AEDN-T1-E3	 SI7806BDN	 SI7806BDN-T1-GE3	 SI7806DN-T1-E3
 SI7806DN-T1-GE3	 SI7810DN	 SI7810DN-T1	 SI7810DN-T1-E	 SI7810DN-T1-E3
 SI7812DN-T1-E3	 SI7812DN-T1-E3	 SI7812DN-T1-GE3	 SI7812DN-T1-GE3	 SI7818DN-T1-E3
 SI7818DN-T1-E3	 SI7820DN-T1-E3	 SI7820DN-T1-E3	 SI7820DN-T1-GE3	 SI7820DN-T1-GE3
 SI7840BDP	 SI7840BDP-T1-E3	 SI7840BDP-T1-E3	 SI7840BDP-T1-GE3	 SI7840BDP-T1-GE3
 SI7840DP	 SI7840DP-T1	 SI7840DP-T1-E3	 SI7840DP-T1-GE3	 SI7840DP-T1-GE3
 SI7842DP	 SI7842DP-T1-E3	 SI7842DP-T1-E3	 SI7842DP-T1-GE3	 SI7842DP-T1-GE3

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

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